

Manuel Cardona

List of Publications by Year in descending order

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196
papers

20,526
citations

16411

64
h-index

11288

136
g-index

200
all docs

200
docs citations

200
times ranked

10337
citing authors

#	ARTICLE	IF	CITATIONS
1	On the value of author indices. Physics Today, 2011, 64, 9-10.	0.3	1
2	Full-zone analysis of relativistic spin splitting at band anticrossings: The case of zinc-blende semiconductors. Physical Review B, 2010, 81, .	1.1	17
3	Isotope effects on the lattice parameter of cubic SiC. Physical Review B, 2009, 79, .	1.1	10
4	The citation impact outside references " formal versus informal citations. Scientometrics, 2009, 80, 1-21.	1.6	16
5	Dielectric constant and long-wavelength refractive index vs. pressure and temperature in semiconductors. High Pressure Research, 2009, 29, 469-475.	0.4	0
6	Path-integral molecular dynamics simulation of $3C$ SiC. Physical Review B, 2008, 77, .	1.1	28
7	Optical Properties II. Graduate Texts in Physics, 2005, , 345-426.	0.1	3
8	Effect of isotope substitution and doping on the Raman spectrum of galena (PbS). Solid State Communications, 2005, 134, 565-570.	0.9	48
9	Isotope effects on the optical spectra of semiconductors. Reviews of Modern Physics, 2005, 77, 1173-1224.	16.4	380
10	Electron-phonon interaction in tetrahedral semiconductors. Solid State Communications, 2005, 133, 3-18.	0.9	140
11	The disaster of the Nazi-power in science as reflected by some leading journals and scientists in physics.. Scientometrics, 2005, 64, 313-324.	1.6	5
12	Photoelectron Spectroscopy. Graduate Texts in Physics, 2005, , 427-468.	0.1	0
13	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors. Graduate Texts in Physics, 2005, , 469-551.	0.1	0
14	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. Graduate Texts in Physics, 2005, , 107-158.	0.1	0
15	Optical Properties I. Graduate Texts in Physics, 2005, , 243-343.	0.1	4
16	Electronic Band Structures. Graduate Texts in Physics, 2005, , 17-105.	0.1	0
17	Temperature Dependence of the Energy Gap of Semiconductors in the Low-Temperature Limit. Physical Review Letters, 2004, 92, 196403.	2.9	75
18	Phonons, Electrons, and Electron-Phonon Interaction: Semiconductors and High-Tc Superconductors. , 2002, , 257-293.		3

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19	First- and second-order Raman spectra of galena (PbS). Journal of Applied Physics, 2002, 92, 4375-4380.	1.1	144
20	Dependence of the excitation energies of boron in diamond on isotopic mass. Solid State Communications, 2001, 121, 7-8.	0.9	14
21	Correlation between the Josephson coupling energy and the condensation energy in bilayer cuprate superconductors. Physical Review B, 2001, 64, .	1.1	38
22	Phonons in isotopically modified semiconductors and high Tc superconductors. Physica B: Condensed Matter, 1999, 263-264, 376-380.	1.3	10
23	First principles calculation of the real part of phonon self energy in compound semiconductors. Physica B: Condensed Matter, 1999, 263-264, 687-690.	1.3	24
24	Raman scattering in high Tc superconductors: phonons, electrons, and electron-phonon interaction. Physica C: Superconductivity and Its Applications, 1999, 317-318, 30-54.	0.6	51
25	Title is missing!. Journal of Low Temperature Physics, 1999, 117, 1049-1053.	0.6	4
26	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. , 1999, , 99-147.		3
27	Optical Properties I. , 1999, , 233-331.		6
28	Photoelectron Spectroscopy. , 1999, , 415-455.		0
29	Optical Properties II. , 1999, , 333-413.		4
30	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors. , 1999, , 457-535.		0
31	Electronic Band Structures. , 1999, , 13-98.		0
32	Ellipsometric investigations of piezo-optical effects. Thin Solid Films, 1998, 313-314, 10-17.	0.8	10
33	Phonons, Strains, and Pressure in Semiconductors. Semiconductors and Semimetals, 1998, 55, 117-233.	0.4	41
34	Isotopic Mass and Lattice Constant: X-ray Standing Wave Measurements. , 1998, 282, 930-932.		64
35	Infrared absorption in amorphous silicon from ab initio molecular dynamics. Applied Physics Letters, 1997, 71, 2692-2694.	1.5	40
36	Effects of isotopic composition on the lattice dynamics of CuCl. Physical Review B, 1997, 56, 210-220.	1.1	73

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37	Isotopic effects on the lattice constant in compound semiconductors by perturbation theory: Anab initio calculation. Physical Review B, 1996, 54, 11305-11310.	1.1	93
38	Electron-phonon interaction at the direct gap of the copper halides. Solid State Communications, 1996, 98, 27-30.	0.9	32
39	Fundamentals of Semiconductors. , 1996, , .		1,007
40	Optical Properties I. , 1996, , 233-331.		6
41	Optical Properties II. , 1996, , 333-413.		1
42	Electronic Band Structures. , 1996, , 13-98.		0
43	Photoelectron Spectroscopy. , 1996, , 415-455.		0
44	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. , 1996, , 99-147.		0
45	Raman Scattering in Semiconductors with Reduced Translational Invariance. Kluwer International Series in Engineering and Computer Science, 1996, , 141-163.	0.2	0
46	Raman scattering by electronic excitations in semiconductors and in highT c superconductors. Journal of Low Temperature Physics, 1995, 99, 205-221.	0.6	46
47	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Thin Solid Films, 1993, 233, 185-188.	0.8	14
48	Linear optical response of semiconductors. Journal of Electronic Materials, 1993, 22, 27-37.	1.0	4
49	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Physical Review B, 1993, 48, 7915-7929.	1.1	79
50	Self-consistent calculation of intervalley deformation potentials in GaAs and Ge. Journal of Applied Physics, 1993, 74, 2117-2119.	1.1	14
51	Effect of heavy doping on the optical properties and band structure of GaAs. Physical Review B, 1993, 47, 7071-7079.	1.1	30
52	Problems in Optical Properties of Semiconductors and their Solutions. , 1993, , 435-473.		0
53	Isotope and temperature shifts of direct and indirect band gaps in diamond-type semiconductors. Physical Review B, 1992, 45, 3376-3385.	1.1	108
54	Alloy versus phonon contributions to intervalley scattering in Al _{1-x} Ga _x As. , 1992, 1677, 75.		3

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55	Temperature dependence of the dielectric function and the interband critical-point parameters of GaSb. <i>Physical Review B</i> , 1991, 43, 4349-4360.	1.1	77
56	The temperature dependence of the band gaps in InP, InAs, InSb, and GaSb. <i>Solid State Communications</i> , 1991, 77, 485-488.	0.9	49
57	Raman scattering in high-Tc superconductors. <i>Physica C: Superconductivity and Its Applications</i> , 1991, 185-189, 65-71.	0.6	27
58	Microscopic theory of intervalley scattering in InP. <i>Physical Review B</i> , 1991, 44, 13446-13451.	1.1	18
59	Intervalley scattering times from the rigid-pseudoion method. , 1990, 1282, 78.		7
60	Effective intervalley deformation potentials in the description of time-resolved and hot-electron luminescence. <i>Solid State Communications</i> , 1990, 76, 877-879.	0.9	23
61	Conduction band minima of InP: Ordering and absolute energies. <i>Applied Physics Letters</i> , 1990, 57, 2339-2341.	1.5	13
62	Ultrafast initial relaxation of hot electrons and holes in tetrahedral semiconductors via deformation potential interaction: Theory and experiment. <i>Applied Physics Letters</i> , 1990, 57, 2838-2840.	1.5	19
63	Microscopic theory of intervalley scattering in GaAs: k dependence of deformation potentials and scattering rates. <i>Journal of Applied Physics</i> , 1990, 68, 1682-1693.	1.1	126
64	Are transverse phonons important for $\hat{\Gamma}^c$ - X-intervalley scattering?. <i>Solid-State Electronics</i> , 1989, 32, 1585-1589.	0.8	22
65	Intervalley deformation potentials and scattering rates in zinc blende semiconductors. <i>Applied Physics Letters</i> , 1989, 54, 614-616.	1.5	84
66	The dielectric function of AlSb from 1.4 to 5.8 eV determined by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1989, 66, 383-387.	1.1	74
67	Raman spectroscopy of vibrations in superlattices. , 1989, , 49-152.		132
68	Temperature Dependence of the Band Structure of Semiconductors: Electron-Phonon Interaction. <i>Physics and Chemistry of Materials With Low-dimensional Structures</i> , 1989, , 51-64.	1.0	16
69	Resonant Raman Scattering in Semiconductors. <i>Physica Scripta</i> , 1989, T25, 201-205.	1.2	6
70	X1 and X3 states of electrons and phonons in zincblende type semiconductors. <i>Solid State Communications</i> , 1988, 67, 927-930.	0.9	33
71	Comment on $\hat{\Gamma}^c$ -Spectroscopy of excited states in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ -InP single quantum wells grown by chemical-beam epitaxy. <i>Physical Review B</i> , 1988, 37, 1011-1012.	1.1	30
72	Spin relaxation of holes in the split-hole band of InP and GaSb. <i>Physical Review B</i> , 1987, 35, 3843-3853.	1.1	14

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73	Resonant Raman scattering by LO phonons near the $E_0 + \Gamma_0$ gap of GaSb. Physical Review B, 1987, 35, 9619-9624.	1.1	21
74	Resonant Raman scattering by plasmons and LO phonons near the E_1 and $E_1 + \Gamma_1$ gaps of GaSb. Physical Review B, 1987, 36, 7469-7485.	1.1	32
75	Acoustic deformation potentials and heterostructure band offsets in semiconductors. Physical Review B, 1987, 35, 6182-6194.	1.1	522
76	Vibrations in amorphous silicon and its alloys. Journal of Molecular Structure, 1986, 141, 93-107.	1.8	17
77	Comment on $\tilde{\epsilon}$ -factor anisotropy of conduction electrons in InSb ϵ^{TM} . Physical Review B, 1986, 34, 7402-7403.	1.1	15
78	Resonant Raman scattering and interference effects of LO phonons at the $E_0 + \Gamma_0$ gap of InP. Physical Review B, 1986, 33, 5473-5481.	1.1	65
79	Dependence of the direct energy gap of GaP on hydrostatic pressure. Solid State Communications, 1985, 55, 327-331.	0.9	49
80	Light emission at the E_1 and $E_1 + \Gamma_1$ gaps in heavily doped p-type Ge and GaAs. Solid State Communications, 1985, 56, 549-552.	0.9	1
81	Electron and phonon self-energies in heavily doped germanium and silicon. Solid-State Electronics, 1985, 28, 31-38.	0.8	1
82	Resonant Raman Scattering by Spin-Density Fluctuations in n-type Germanium. Physical Review Letters, 1985, 55, 1132-1135.	2.9	12
83	Resonance Raman scattering by LO phonons in $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ at the $E_0 + \Gamma_0$ gap. Physical Review B, 1985, 31, 3705-3711.	1.1	69
84	Electronic Raman scattering in heavily doped p-type germanium. Physical Review B, 1985, 32, 8071-8077.	1.1	19
85	Interference effects: A key to understanding forbidden Raman scattering by LO phonons in GaAs. Physical Review B, 1985, 31, 3696-3704.	1.1	162
86	Light scattering by plasmons in germanium. Physical Review B, 1984, 29, 3737-3739.	1.1	20
87	Electron-phonon interaction and phonon softening in ferro-electrics and semiconductors. Ferroelectrics, 1984, 53, 49-58.	0.3	5
88	Resonant Raman scattering by plasmons in n-type Ge. Solid State Communications, 1984, 49, 1103-1105.	0.9	3
89	Temperature dependence of the first-order Raman scattering by phonons in Si, Ge, and $\pm\text{Sn}$: Anharmonic effects. Physical Review B, 1984, 29, 2051-2059.	1.1	714
90	Light scattering by free carrier excitations in semiconductors. Topics in Applied Physics, 1984, , 5-150.	0.4	135

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91	Optical constants of pure and heavily doped silicon and germanium: Electronic interband transitions. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 117-118, 356-358.	0.9	2
92	Interference between Allowed and Forbidden Raman Scattering by Longitudinal-Optical Phonons in GaAs. <i>Physical Review Letters</i> , 1983, 51, 1297-1299.	2.9	56
93	Vibrational spectra of Si, H, a-Si, F, and Ge: F: Bethe-lattice calculations. <i>Physical Review B</i> , 1983, 28, 880-888.	1.1	27
94	Pressure dependence of Raman phonons of Ge and 3C-SiC. <i>Physical Review B</i> , 1982, 25, 1151-1160.	1.1	183
95	Temperature dependence of the optical phonons and transverse effective charge in 3C-SiC. <i>Physical Review B</i> , 1982, 25, 3889-3896.	1.1	92
96	Self-energy effects of the optical phonons of heavily doped α -GaAs and α -Ge. <i>Physical Review B</i> , 1981, 23, 6592-6602.	1.1	90
97	Raman scattering by two LO-phonons near Γ in GaAs. <i>Solid State Communications</i> , 1981, 39, 1071-1075.	0.9	28
98	A new application of the diamond anvil cell: Measurements under uniaxial stress. <i>Solid State Communications</i> , 1981, 38, 1109-1112.	0.9	11
99	Resonant spin-flip Raman scattering on donor and acceptor states in ZnTe. <i>Physical Review B</i> , 1981, 23, 4129-4139.	1.1	47
100	Intra- and inter-valence-band electronic Raman scattering in heavily doped p-GaAs. <i>Physical Review B</i> , 1980, 22, 1905-1911.	1.1	17
101	Photoluminescence in heavily doped GaAs. II. Hydrostatic pressure dependence. <i>Physical Review B</i> , 1980, 22, 894-903.	1.1	83
102	Electronic properties of clean and oxygen covered (100) cleaved surfaces of PbS. <i>Surface Science</i> , 1980, 92, 385-392.	0.8	22
103	Photoluminescence in heavily doped GaAs. I. Temperature and hole-concentration dependence. <i>Physical Review B</i> , 1980, 22, 886-893.	1.1	164
104	Luminescence above the gap in heavily Zn-doped GaAs. <i>Solid State Communications</i> , 1979, 32, 1027-1030.	0.9	10
105	Temperature effects on valence bands in semiconducting lead chalcogenides. <i>Solid State Communications</i> , 1979, 32, 353-356.	0.9	11
106	Raman scattering in pure and hydrogenated amorphous germanium and silicon. <i>Journal of Non-Crystalline Solids</i> , 1979, 32, 405-419.	1.5	200
107	Infrared absorption in hydrogenated amorphous and crystallized germanium. <i>Journal of Non-Crystalline Solids</i> , 1979, 32, 421-430.	1.5	86
108	Piezoresistance and the conduction-band minima of GaAs. <i>Physical Review B</i> , 1978, 17, 741-751.	1.1	42

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109	Strain dependence of effective masses in tetrahedral semiconductors. Physical Review B, 1978, 17, 726-740.	1.1	48
110	Angle-resolved uv photoemission and electronic band structures of the lead chalcogenides. Physical Review B, 1978, 18, 3847-3871.	1.1	130
111	Effect of hydrostatic pressure on the direct absorption edge of germanium. Physical Review B, 1977, 15, 875-879.	1.1	63
112	Valence Band Structure of PbS from Angle-Resolved Photoemission. Physical Review Letters, 1977, 38, 1033-1036.	2.9	55
113	Intraband Raman scattering by free carriers in heavily doped n -Si. Physical Review B, 1977, 16, 3579-3595.	1.1	59
114	Transverse reduced mass of the E_1 and $E_1 + \hbar\omega_1$ transitions in silicon. Physical Review B, 1977, 15, 5999-6000.	1.1	31
115	Resonant Raman scattering in ZnO. Physical Review B, 1977, 16, 3753-3761.	1.1	780
116	Infrared and Raman spectra of the silicon-hydrogen bonds in amorphous silicon prepared by glow discharge and sputtering. Physical Review B, 1977, 16, 3556-3571.	1.1	1,577
117	Resonant Raman scattering in the II-IV semiconductors Mg_2Si , Mg_2Ge , and Mg_2Sn . Physical Review B, 1976, 14, 3520-3531.	1.1	36
118	Valence bands of the Mg_2X ($X=Si, Ge, Sn$) semiconducting compounds. Physical Review B, 1976, 14, 2559-2568.	1.1	44
119	Effect of free carriers on the elastic constants of p -type silicon and germanium. Physical Review B, 1976, 13, 5429-5441.	1.1	24
120	Dependence of the indirect energy gap of silicon on hydrostatic pressure. Solid State Communications, 1975, 17, 1021-1024.	0.9	91
121	Dependence of the direct energy gap of GaAs on hydrostatic pressure. Physical Review B, 1975, 12, 5729-5738.	1.1	302
122	Bond Charge, Bond Polarizability, and Phonon Spectra in Semiconductors. Physical Review Letters, 1975, 34, 580-583.	2.9	138
123	Densities of valence states of amorphous and crystalline III-V and II-VI semiconductors. Physical Review B, 1974, 9, 2627-2648.	1.1	234
124	Interaction between electronic and vibronic Raman scattering in heavily doped silicon. Solid State Communications, 1973, 13, 325-328.	0.9	79
125	Elastic constants and Raman frequencies of heavily doped Si under uniaxial stress. Solid State Communications, 1973, 12, 553-556.	0.9	7
126	Light scattering as a form of modulation spectroscopy. Surface Science, 1973, 37, 100-119.	0.8	52

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127	Effects of Free Carriers on Zone-Center Vibrational Modes in Heavily Doped p-type Si. I. Acoustical Modes. <i>Physical Review B</i> , 1973, 8, 4723-4733.	1.1	32
128	Resonant First- and Second-Order Raman Scattering in GaP. <i>Physical Review B</i> , 1973, 8, 2795-2809.	1.1	117
129	Second-Order Raman Spectrum of Germanium. <i>Physical Review B</i> , 1973, 7, 2545-2551.	1.1	113
130	Effect of Carrier Concentration on the Raman Frequencies of Si and Ge. <i>Physical Review B</i> , 1972, 5, 1440-1454.	1.1	211
131	Stress-Induced Shifts of First-Order Raman Frequencies of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1972, 5, 580-593.	1.1	842
132	Two-phonon Raman spectra of Si and GaP. <i>Solid State Communications</i> , 1972, 10, 961-965.	0.9	39
133	Resonant Raman scattering in germanium. <i>Solid State Communications</i> , 1972, 10, 591-595.	0.9	93
134	X-ray and far ultraviolet photoemission of AlSb. <i>Solid State Communications</i> , 1972, 11, 1619-1623.	0.9	30
135	Photoemission of GaAs and InSb core levels. <i>Solid State Communications</i> , 1972, 11, 1655-1658.	0.9	18
136	Resonant Raman scattering in germanium and zincblende-type semiconductors temperature dependence. <i>Solid State Communications</i> , 1971, 9, 1235-1238.	0.9	16
137	Spatial dispersion in the dielectric constant of GaAs. <i>Solid State Communications</i> , 1971, 9, 1421-1424.	0.9	66
138	Effects of Uniaxial Stress on the Indirect Exciton Spectrum of Silicon. <i>Physical Review B</i> , 1971, 3, 2623-2636.	1.1	228
139	Modulation Spectroscopy of Semiconductors. , 1970, , 125-173.		26
140	Optical Properties of Some Compound Semiconductors in the 36-150-eV Region. <i>Physical Review B</i> , 1970, 1, 2605-2612.	1.1	56
141	Deformation Potentials of the Indirect and Direct Absorption Edges of AlSb. <i>Physical Review B</i> , 1970, 1, 1436-1442.	1.1	46
142	Energy-Band Structure and Optical Spectrum of Grey Tin. <i>Physical Review B</i> , 1970, 2, 352-363.	1.1	76
143	Anomalous Behavior of ϵ_3 near T_c for Sn-In and In-Bi Alloy Systems. <i>Physical Review B</i> , 1970, 2, 2512-2519.	1.1	7
144	Modulated Piezoreflectance in Semiconductors. <i>Physical Review B</i> , 1970, 1, 672-682.	1.1	174

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145	Modulation spectroscopy of semiconductors. , 1970, , 125-173.		8
146	Transverse electroreflectance in semi-insulating silicon and gallium arsenide. Journal of Physics and Chemistry of Solids, 1970, 31, 227-246.	1.9	54
147	Temperature Coefficient of the Refractive Index of Diamond- and Zinc-Blende-Type Semiconductors. Physical Review B, 1970, 2, 3193-3197.	1.1	114
148	Piezobirefringence and Deformation Potentials of the Alkali Halides. Physical Review, 1969, 177, 1351-1357.	2.7	47
149	Variation of the Ratio H_c3H_c2 in the Immediate Vicinity of T_c . Physical Review, 1969, 187, 766-767.	2.7	13
150	Stress-Induced Exchange Splitting of Hyperbolic Excitons in GaAs.. Physical Review Letters, 1969, 22, 933-936.	2.9	50
151	Photorefectance and electroreflectance in silicon. Solid State Communications, 1969, 7, 879-882.	0.9	32
152	Intrinsic piezobirefringence of AlSb. Solid State Communications, 1969, 7, 1113-1117.	0.9	15
153	Derivative spectrum of indirect excitons in AlSb. Solid State Communications, 1969, 7, 441-444.	0.9	22
154	Intrinsic Piezobirefringence of Ge, Si, and GaAs. Physical Review, 1969, 184, 821-829.	2.7	158
155	Optical Constants of Insulators: Dispersion Relations. , 1969, , 137-151.		24
156	Valence band symmetry and deformation potentials of ZnO. Solid State Communications, 1968, 6, 239-242.	0.9	61
157	Thermorefectance in the alkali metals. Solid State Communications, 1968, 6, 313-316.	0.9	13
158	Electroreflectance Measurements on Mg_2Si , Mg_2Ge , and Mg_2Sn . Physical Review, 1968, 176, 905-908.	2.7	66
159	New Evidence for the Existence of Exciton Effects at Hyperbolic Critical Points. Physical Review, 1968, 174, 828-830.	2.7	81
160	Piezo-Electroreflectance in Ge, GaAs, and Si. Physical Review, 1968, 172, 816-837.	2.7	835
161	Thermorefectance in Semiconductors. Physical Review, 1968, 176, 950-960.	2.7	265
162	Chapter 5 Optical Absorption above the Fundamental Edge. Semiconductors and Semimetals, 1967, 3, 125-151.	0.4	13

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163	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review</i> , 1967, 154, 696-720.	2.7	761
164	Band structure of gray tin under uniaxial stress. <i>Solid State Communications</i> , 1967, 5, 233-235.	0.9	24
165	Optical constants of germanium and gray tin the . method. <i>Solid State Communications</i> , 1967, 5, 513-516.	0.9	26
166	Energy band structure of germanium and gallium arsenide: The . method. <i>Journal of Physics and Chemistry of Solids</i> , 1966, 27, 423-425.	1.9	34
167	Electroreflectance and band structure of gray tin. <i>Solid State Communications</i> , 1966, 4, 319-321.	0.9	40
168	Electronic surface states in germanium and silicon. <i>Solid State Communications</i> , 1966, 4, 271-274.	0.9	27
169	Energy-Band Structure of Germanium and Silicon: The $k\text{-p}$ Method. <i>Physical Review</i> , 1966, 142, 530-543.	2.7	598
170	Electroreflectance in AlSb: Observation of the Direct Band Edge. <i>Physical Review Letters</i> , 1966, 16, 644-646.	2.9	37
171	Electroreflectance and Spin-Orbit Splitting in III-V Semiconductors. <i>Physical Review Letters</i> , 1966, 16, 48-50.	2.9	54
172	Piezoelectroreflectance in GaAs. <i>Physical Review Letters</i> , 1966, 16, 942-944.	2.9	48
173	Electroreflectance in the GaAs-GaP Alloys. <i>Physical Review</i> , 1966, 146, 601-610.	2.7	169
174	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review Letters</i> , 1965, 15, 883-885.	2.9	106
175	Infrared Dielectric Constant and Ultraviolet Optical Properties of Solids with Diamond, Zinc Blende, Wurtzite, and Rocksalt Structure. <i>Journal of Applied Physics</i> , 1965, 36, 2181-2186.	1.1	95
176	Ultraviolet Reflection Spectrum of Cubic CdS. <i>Physical Review</i> , 1965, 140, A633-A637.	2.7	136
177	Optical Properties and Band Structure of Wurtzite-Type Crystals and Rutile. <i>Physical Review</i> , 1965, 137, A1467-A1476.	2.7	523
178	Optical Properties and Band Structure of SrTiO ₃ and BaTiO ₃ . <i>Physical Review</i> , 1965, 140, A651-A655.	2.7	730
179	Evidence for Normal Regions at Low Temperatures in the Superconducting Mixed State. <i>Physical Review Letters</i> , 1964, 12, 657-659.	2.9	65
180	Microwave Surface Impedance of Superconductors of the Second Kind: In-Bi Alloys. <i>Physical Review Letters</i> , 1964, 12, 101-103.	2.9	25

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181	Optical Properties and Band Structure of Group IV-VI and Group V Materials. Physical Review, 1964, 133, A1685-A1697.	2.7	397
182	Polarization effects in the ultraviolet reflection of crystals with wurtzite structure. Solid State Communications, 1963, 1, 109-115.	0.9	39
183	Band parameters of semiconductors with zincblende, wurtzite, and germanium structure. Journal of Physics and Chemistry of Solids, 1963, 24, 1543-1555.	1.9	434
184	Absorption Spectrum of Germanium and Zinc-Blende-Type Materials at Energies Higher than the Fundamental Absorption Edge. Journal of Applied Physics, 1963, 34, 813-818.	1.1	168
185	Fundamental Reflectivity and Band Structure of ZnTe, CdTe, and HgTe. Physical Review, 1963, 131, 98-103.	2.7	273
186	Optical Properties of the Silver and Cuprous Halides. Physical Review, 1963, 129, 69-78.	2.7	578
187	Resonances of a Small Plasma Sphere in a Magnetic Field. Physical Review, 1963, 129, 991-997.	2.7	29
188	Reflectivity of Semiconductors with Wurtzite Structure. Physical Review, 1963, 129, 1068-1069.	2.7	51
189	Excitons at the Absorption Edge in Zinc Blende-Type Semiconductors. Physical Review Letters, 1962, 8, 90-91.	2.9	70
190	Reflectivity of Gray Tin Single Crystals in the Fundamental Absorption Region. Physical Review, 1962, 125, 1291-1296.	2.7	99
191	Faraday rotation in semiconductors. , 1962, , 72-88.		0
192	Electron Effective Masses of InAs and GaAs as a Function of Temperature and Doping. Physical Review, 1961, 121, 752-758.	2.7	197
193	Optical Studies of the Band Structure of InP. Journal of Applied Physics, 1961, 32, 958-958.	1.1	53
194	Fundamental Reflectivity Spectrum of Semiconductors with Zinc-Blende Structure. Journal of Applied Physics, 1961, 32, 2151-2155.	1.1	173
195	Optical investigation of the band structure of GaSb. European Physical Journal A, 1961, 161, 99-102.	1.0	30
196	Effect of Temperature and Doping on the Reflectivity of Germanium in the Fundamental Absorption Region. Physical Review, 1961, 122, 1382-1388.	2.7	86